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November 2013

### **FQL40N50**

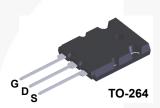
### N-Channel QFET® MOSFET 500 V, 40 A, 110 mΩ

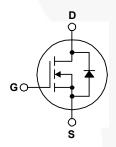
### **Description**

This N-Channel enhancement mode power MOSFET is • 40 A, 500 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 155 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 95 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- $I_D = 20 A$





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQL40N50	Unit
V <sub>DSS</sub>	Drain-Source Voltage		500	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		40	А
	- Continuous (T <sub>C</sub> = 100°C)		25	А
I <sub>DM</sub>	Drain Current - Pulsed	Note 1)	160	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	Note 2)	1780	mJ
I <sub>AR</sub>	Avalanche Current	Note 1)	40	А
E <sub>AR</sub>	Repetitive Avalanche Energy	Note 1)	46	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		4.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		460	W
	- Derate above 25°C		3.7	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>I</sub>	Maximum lead temperature for soldering,		300	°C
· L	1/8" from case for 5 seconds.		300	

### **Thermal Characteristics**

Symbol	Parameter	FQL40N50	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.27	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	30	°C/W	

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQL40N50	FQL40N50	TO-264	Tube	N/A	N/A	25 units

### **Electrical Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C		0.48		V/°C
I <sub>DSS</sub>		V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.085	0.11	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_{D} = 20 \text{ A}$		29		S
Dynami	ic Characteristics				,	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	\	5800	7500	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		880	1150	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			95	120	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 250 \text{ V}, I_{D} = 40 \text{ A},$		140	290	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		440	890	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	- · · · · · · · · · · · · · · · · · · ·		350	700	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		250	500	ns
$Q_g$	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 40 A,		155	200	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		37		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		78		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				40	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				160	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 40 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 40 A,		520		ns
Q <sub>rr</sub>	Payersa Pacovery Charge	verse Recovery Charge dl <sub>F</sub> / dt = 100 A/μs		8.0	//	μС

<sup>1.</sup> Repetitive rating : pulse-width limited by maximum junction temperature.

<sup>2.</sup> L = 2.0 mH, I<sub>AS</sub> = 40 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  40 A, di/dt  $\leq$  200 A/ $\mu$ s , V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

### **Typical Characteristics**

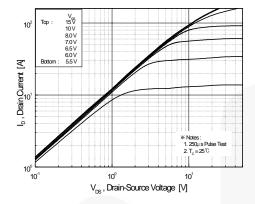


Figure 1. On-Region Characteristics

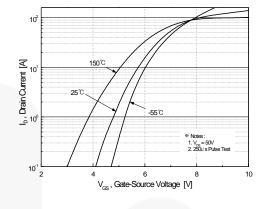


Figure 2. Transfer Characteristics

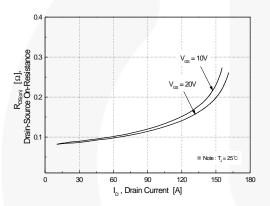


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

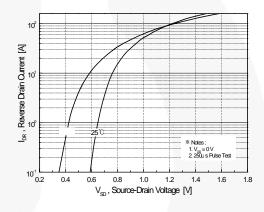


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

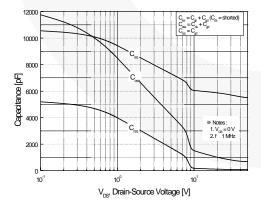


Figure 5. Capacitance Characteristics

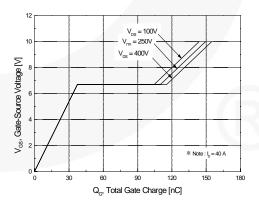


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)

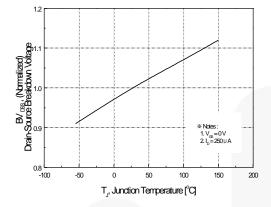


Figure 7. Breakdown Voltage Variation vs. Temperature

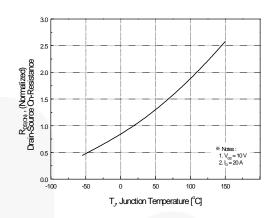


Figure 8. On-Resistance Variation vs. Temperature

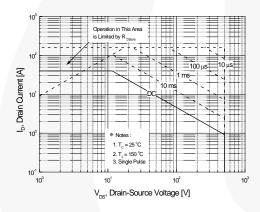


Figure 9. Maximum Safe Operating Area

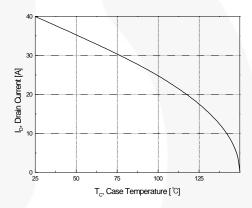


Figure 10. Maximum Drain Current vs. Case Temperature

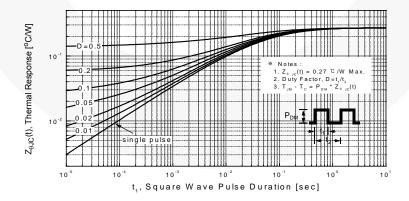


Figure 11. Transient Thermal Response Curve

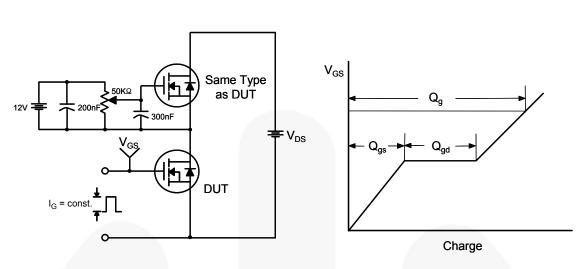


Figure 12. Gate Charge Test Circuit & Waveform

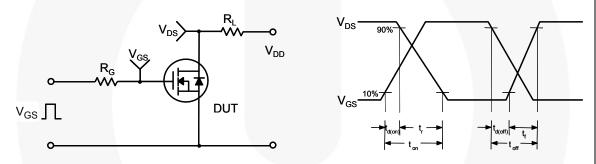


Figure 13. Resistive Switching Test Circuit & Waveforms

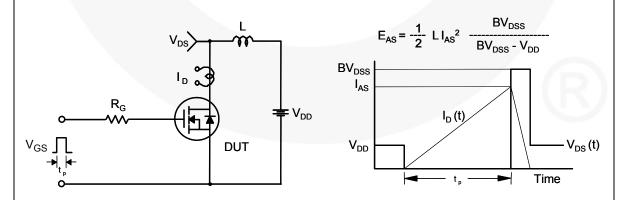
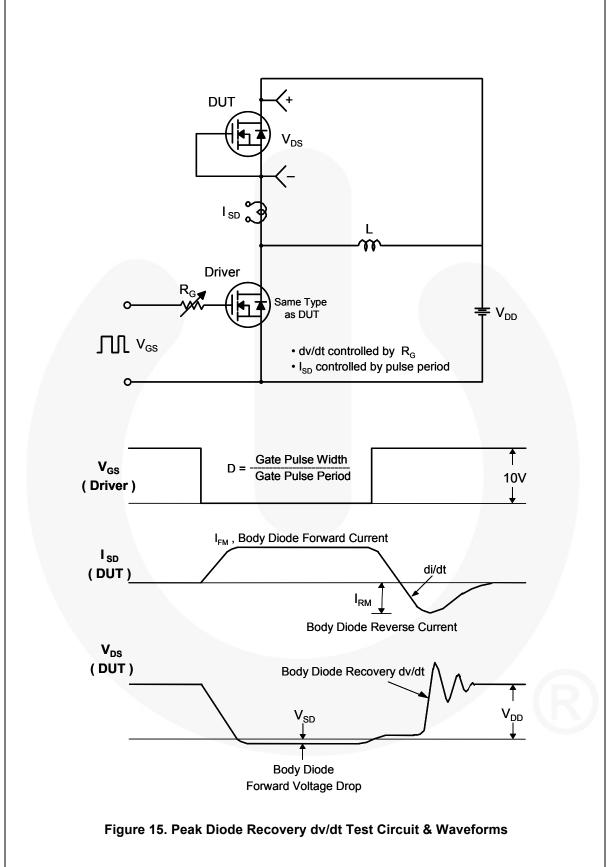
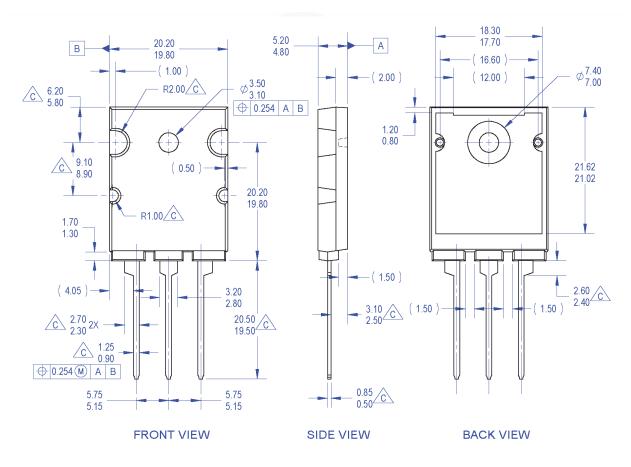
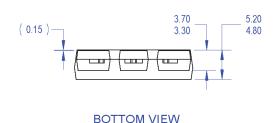


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**





#### NOTES:

- A. PACKAGE REFERENCE: JEDEC TO264 VARIATION AA
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- OUT OF JEDEC STANDARD VALUE.
  DIMENSION AND TOLERANCE AS PER ASME
  Y14.5-1994.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS. F. THIS PACKAGE IS INTENDED ONLY FOR "FS PKG CODE AR"
- G. DRAWING FILE NAME: TO264A03REV1

Figure 16. TO264, Molded, 3-Lead, Jedec Variation AA

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